Dual supply translating transceiver; open-drain; auto direction sensing

Rev. 4.1 — 12 November 2021

Product data sheet

1 General description

The NTS0102 is a 2-bit, dual supply translating transceiver with auto direction sensing, that enables bidirectional voltage level translation. It features two 2-bit input-output ports (An and Bn), one output enable input (OE) and two supply pins (V_{CC(A)} and V_{CC(B)}). V_{CC(A)} can be supplied at any voltage between 1.65 V and 3.6 V and V_{CC(B)} can be supplied at any voltage between 2.3 V and 5.5 V, making the device suitable for translating between any of the voltage nodes (1.8 V, 2.5 V, 3.3 V, and 5.0 V). Pins An and OE are referenced to V_{CC(A)} and pins Bn are referenced to V_{CC(B)}. A LOW level at pin OE causes the outputs to assume a high-impedance OFF-state. This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2 Features and benefits

- Wide supply voltage range:
 - V_{CC(A)}: 1.65 V to 3.6 V and V_{CC(B)}: 2.3 V to 5.5 V
- Maximum data rates:
 - Push-pull: 50 Mbit/s
- I_{OFF} circuitry provides partial Power-down mode operation
- Inputs accept voltages up to 5.5 V
- ESD protection:
 - HBM JESD22-A114E Class 2 exceeds 2500 V for A port
 - HBM JESD22-A114E Class 3B exceeds 8000 V for B port
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1500 V
- Latch-up performance exceeds 100 mA per JESD 78B Class II
- Multiple package options
- Specified from –40 °C to +85 °C and -40 °C to +125 °C

3 Applications

- I²C/SMBus
- UART
- GPIO



Ordering information 4

Type number	Topside	Package					
	marking	Name	Description	Version			
NTS0102DP	s02	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2			
NTS0102GT	s02	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1			
NTS0102GD	s02	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body $3 \times 2 \times 0.5$ mm	SOT996-2			
NTS0102GF	s2	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1 × 0.5 mm	SOT1089			
NTS0102TL	tS2	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 3 x 2 x 0.5 mm	SOT1052-2			

Table 1. Ordering information

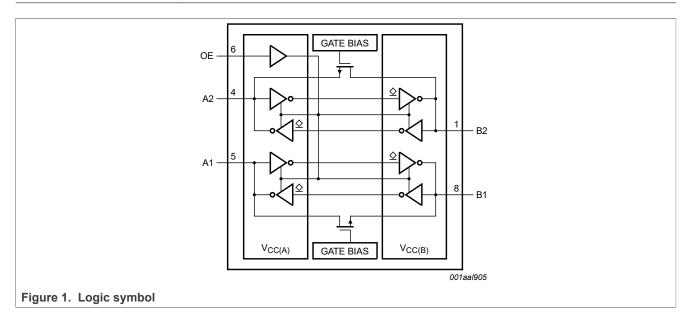
4.1 Ordering options

Table 2. Ordering options

Type number	Orderable part number	Package	Packing method ^[1]	Minimum order quantity	Temperature
NTS0102DP	NTS0102DP,125	TSSOP8	Reel 7" Q3 NDP	3000	–40 °C to +125 °C
NTS0102GT	NTS0102GT,115	XSON8	Reel 7" Q1 NDP	5000	–40 °C to +125 °C
NTS0102GD ^[2]	NTS0102GD,125	XSON8	Reel 7" Q3 NDP	3000	–40 °C to +125 °C
NTS0102GF	NTS0102GF,115	XSON8	Reel 7" Q1 NDP	5000	–40 °C to +125 °C
NTS0102TL	NTS0102TLH	XSON8	Reel 7" Q3 NDP	3000	–40 °C to +125 °C

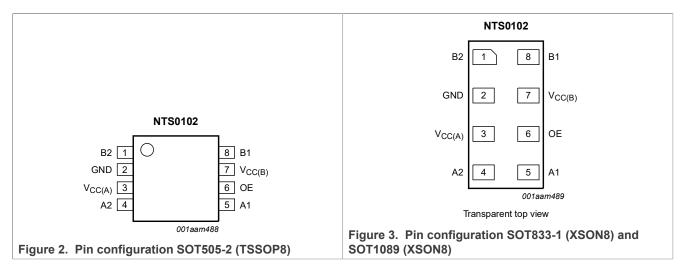
Standard packing quantities and other packaging data are available at www.nxp.com/packages/. Discontinuation Notice 202111012DN - drop in replacement is NTS0102TLH. [1] [2]

5 Functional diagram



6 **Pinning information**

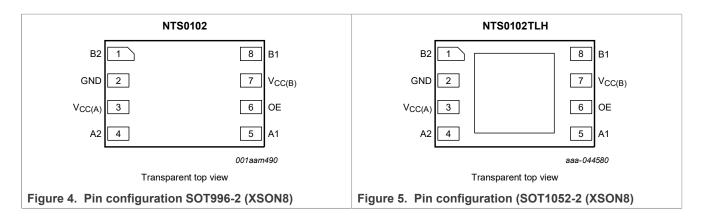
6.1 Pinning



NXP Semiconductors

NTS0102

Dual supply translating transceiver; open-drain; auto direction sensing



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
	SOT505-2, SOT833-1, SOT1089, SOT996-2, and SOT1052-2	
B2, B1	1, 8	data input or output (referenced to $V_{CC(B)}$)
GND	2	ground (0 V)
V _{CC(A)}	3	supply voltage A
A2, A1	4, 5	data input or output (referenced to $V_{CC(A)}$)
OE	6	output enable input (active HIGH; referenced to $V_{CC(A)}$)
V _{CC(B)}	7	supply voltage B
n.c.		not connected

7 Functional description

Table 4. Function table^[1]

Supply voltage		Input	Input/output	
V _{CC(A)}	V _{CC(B)} OE		An	Bn
1.65 V to $V_{CC(B)}$	to V _{CC(B)} 2.3 V to 5.5 V		Z	Z
1.65 V to $V_{CC(B)}$	2.3 V to 5.5 V	Н	input or output	output or input
GND ^[2]	GND ^[2]	X	Z	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

[2] When either $V_{CC(A)}$ or $V_{CC(B)}$ is at GND level, the device goes into power-down mode.

8 Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{CC(A)}	supply voltage A		-0.5	+6.5	V
V _{CC(B)}	supply voltage B		-0.5	+6.5	V
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Symbol	Parameter	Conditions		Min	Мах	Unit
VI	input voltage	A port and OE input		-0.5	+6.5	V
		B port	[1] [2]	-0.5	+6.5	V
Vo	output voltage	Active mode	[1] [2]			
		A or B port		-0.5	V _{CCO} + 0.5	V
		Power-down or 3-state mode	[1]			
		A port		-0.5	+4.6	V
		B port		-0.5	+6.5	V
l _{IK}	input clamping current	V _I < 0 V		-50	—	mA
I _{OK}	output clamping current	V _O < 0 V		-50		mA
I _O	output current	$V_{O} = 0 V$ to V_{CCO}	[2]	—	±50	mA
I _{CC}	supply current	I _{CC(A)} or I _{CC(B)}		—	100	mA
I _{GND}	ground current			-100	—	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	[3]	—	250	mW

Table 5. Limiting values...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

The minimum input and minimum output voltage ratings may be exceeded if the input and output current ratings are observed. [1]

[2] [3]

 V_{CCO} is the supply voltage associated with the output. For TSSOP8 package: above 55 °C, the value of P_{tot} derates linearly with 2.5 mW/K. For XSON8 packages: above 118 °C, the value of Ptot derates linearly with 7.8 mW/K.

9 **Recommended operating conditions**

Table 6. Recommended operating conditions^{[1][2]}

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC(A)}	supply voltage A		1.65	3.6	V
V _{CC(B)}	supply voltage B		2.3	5.5	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV input transition r	input transition rise and fall rate	A or B port; push-pull driving			
		$V_{CC(A)}$ = 1.65 V to 3.6 V; $V_{CC(B)}$ = 2.3 V to 5.5 V	—	10	ns/V
		OE input			
		$V_{CC(A)}$ = 1.65 V to 3.6 V; $V_{CC(B)}$ = 2.3 V to 5.5 V	_	10	ns/V

The A and B sides of an unused I/O pair must be held in the same state, both at V_{CCI} or both at GND. [1]

[2] $V_{CC(A)}$ must be less than or equal to $V_{CC(B)}$.

10 Static characteristics

Table 7. Typical static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T_{amb} = 25 °C.

Symbol	Parameter	Conditions	ľ	Min	Тур	Мах	Unit
I	input leakage current	OE input; V _I = 0 V to 3.6 V; V _{CC(A)} = 1.65 V to 3.6 V; V _{CC(B)} = 2.3 V to 5.5 V	-		_	±1	μA
I _{OZ}	OFF-state output current	A or B port; $V_0 = 0$ V or V_{CCO} ; $V_{CC(A)} = 1.65$ V to 3.6 V; $V_{CC(B)} = 2.3$ V to 5.5 V	[1] _		_	±1	μA
I _{OFF}	power-off leakage current	A port; V ₁ or V ₀ = 0 V to 3.6 V; V _{CC(A)} = 0 V; V _{CC(B)} = 0 V to 5.5 V	-			±1	μA
		B port; V _I or V _O = 0 V to 5.5 V; V _{CC(B)} = 0 V; V _{CC(A)} = 0 V to 3.6 V	-		_	±1	μA
CI	input capacitance	OE input; $V_{CC(A)}$ = 3.3 V; $V_{CC(B)}$ = 3.3 V	-		1	_	pF
C _{I/O}	input/output	A port	-		5	_	pF
	capacitance	B port	-		8.5	-	pF
		A or B port; $V_{CC(A)}$ = 3.3 V; $V_{CC(B)}$ = 3.3 V	-		11	—	pF

[1] V_{CCO} is the supply voltage associated with the output.

Table 8. Typical supply current

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T_{amb} = 25 °C.

V _{CC(A)}	V _{CC(B)}	V _{CC(B)}							
	2.5 V	2.5 V		3.3 V		5.0 V			
	I _{CC(A)}	I _{CC(B)}	I _{CC(A)}	I _{CC(B)}	I _{CC(A)}	I _{CC(B)}			
1.8 V	0.1	0.5	0.1	1.5	0.1	4.6	μA		
2.5 V	0.1	0.1	0.1	0.8	0.1	3.8	μA		
3.3 V	_		0.1	0.1	0.1	2.8	μA		

Table 9. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to	-40 °C to +85 °C		-40 °C to +125 °C	
			Min	Max	Min	Max	
V _{IH} HIGH-level input voltage		A port					
	input voltage	$V_{CC(A)} = 1.65 V \text{ to } 1.95 V;$ $V_{CC(B)} = 2.3 V \text{ to } 5.5 V$	V _{CCI} - 0.2		V _{CCI} - 0.2	_	V
		$V_{CC(A)} = 2.3 \text{ V to } 3.6 \text{ V}; V_{CC(B)}$ = 2.3 V to 5.5 V	^I V _{CCI} - 0.4	—	V _{CCI} - 0.4	—	V
		B port					
		$V_{CC(A)} = 1.65 V \text{ to } 3.6 V; V_{CC(B)}$ [1] = 2.3 V to 5.5 V	V _{CCI} - 0.4		V _{CCI} - 0.4	—	V
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Table 9. Static characteristics...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		-40 °C te	o +85 °C	-40 °C to	Unit	
				Min	Max	Min	Max]
		OE input						
		V _{CC(A)} = 1.65 V to 3.6 V; V _{CC(B)} = 2.3 V to 5.5 V		0.65V _{CC(A)}	_	0.65V _{CC(A)}	-	V
V _{IL}	LOW-level	A or B port						
	input voltage	$V_{CC(A)}$ = 1.65 V to 3.6 V; $V_{CC(B)}$ = 2.3 V to 5.5 V			0.15	_	0.15	V
		OE input						
		V _{CC(A)} = 1.65 V to 3.6 V; V _{CC(B)} = 2.3 V to 5.5 V			0.35V _{CC(A)}		0.35V _{CC(A)}	V
V _{OH}	HIGH-level	Ι _O = -20 μΑ						
	output voltage	$V_{CC(A)}$ = 1.65 V to 3.6 V; $V_{CC(B)}$ = 2.3 V to 5.5 V	[2]	0.67V _{CCO}	_	0.67V _{CCO}	_	V
V _{OL}	LOW-level	A or B port; I _O = 1 mA	[2]					
	output voltage	$V_{I} \leq 0.15 \text{ V}; V_{CC(A)} = 1.65 \text{ V to} \\ 3.6 \text{ V}; V_{CC(B)} = 2.3 \text{ V to } 5.5 \text{ V}$			0.4	_	0.4	V
I	input leakage current	OE input; $V_I = 0 V$ to 3.6 V; $V_{CC(A)} = 1.65 V$ to 3.6 V; $V_{CC(B)} = 2.3 V$ to 5.5 V			±2		±12	μA
I _{OZ}	OFF-state output current	A or B port; $V_0 = 0 V \text{ or } V_{CCO}$; $V_{CC(A)} = 1.65 V \text{ to } 3.6 V$; $V_{CC(B)} = 2.3 V \text{ to } 5.5 V$	[2]		±2		±12	μA
I _{OFF}	power-off leakage	A port; V ₁ or V ₀ = 0 V to 3.6 V; V _{CC(A)} = 0 V; V _{CC(B)} = 0 V to 5.5 V			±2		±12	μA
	current	B port; V _I or V _O = 0 V to 3.6 V; V _{CC(B)} = 0 V; V _{CC(A)} = 0 V to 3.6 V			±2		±12	μA
I _{CC}	supply current	$V_{I} = 0 V \text{ or } V_{CCI}; I_{O} = 0 A$	[1]					
		I _{CC(A)}						
		V _{CC(A)} = 1.65 V to 3.6 V; V _{CC(B)} = 2.3 V to 5.5 V			2.4		15	μA
		V _{CC(A)} = 3.6 V; V _{CC(B)} = 0 V			2.2		15	μA
		V _{CC(A)} = 0 V; V _{CC(B)} = 5.5 V		_	-1		-8	μA
		I _{CC(B)}						
		$V_{CC(A)}$ = 1.65 V to 3.6 V; $V_{CC(B)}$ = 2.3 V to 5.5 V			12		30	μA
		V _{CC(A)} = 3.6 V; V _{CC(B)} = 0 V			-1		-5	μA
		V _{CC(A)} = 0 V; V _{CC(B)} = 5.5 V			1		6	μA
		$I_{CC(A)} + I_{CC(B)}$						
		V _{CC(A)} = 1.65 V to 3.6 V; V _{CC(B)} = 2.3 V to 5.5 V		—	14.4	_	30	μA

 V_{CCI} is the supply voltage associated with the input. V_{CCO} is the supply voltage associated with the output. [1]

[2]

11 Dynamic characteristics

Table 10. Dynamic characteristics for temperature range -40 $^{\circ}\text{C}$ to +85 $^{\circ}\text{C}^{[1]}$ Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 8; for wave forms see Figure 6 and Figure 7.

Symbol	Parameter	Conditions	V _{CC(B)}						
			2.5 V	± 0.2 V	3.3 V	± 0.3 V	5.0 V ± 0.5 V		
			Min	Max	Min	Max	Min	Max	_
V _{CC(A)} =	1.8 V ± 0.15 V								
t _{PHL}	HIGH to LOW propagation delay	A to B	—	4.6		4.7	_	5.8	ns
t _{PLH}	LOW to HIGH propagation delay	A to B	_	6.8		6.8	_	7.0	ns
t _{PHL}	HIGH to LOW propagation delay	B to A	—	4.4	_	4.5	_	4.7	ns
t _{PLH}	LOW to HIGH propagation delay	B to A	_	5.3	_	4.5	_	0.5	ns
t _{en}	enable time	OE to A; B	_	200		200	—	200	ns
t _{dis}	disable time	OE to A; no external load ^[2]		25		25	—	25	ns
		OE to B; no external load ^[2]		25		25	_	25	ns
		OE to A		230		230	_	230	ns
		OE to B	_	200		200	—	200	ns
t _{TLH} LOW to HIGH		A port	3.2	9.5	2.3	9.3	1.8	7.6	ns
	output transition time	B port	3.3	10.8	2.7	9.1	2.7	7.6	ns
t _{THL}	HIGH to LOW	A port	2.0	5.9	1.9	6.0	1.7	13.3	ns
	output transition time	B port	2.9	7.6	2.8	7.5	2.8	10.0	ns
t _{sk(o)}	output skew time	between channels [3]		0.7		0.7	—	0.7	ns
t _W	pulse width	data inputs	20		20	—	20		ns
f _{data}	data rate			50		50	—	50	Mbit/s
V _{CC(A)} =	2.5 V ± 0.2 V								
t _{PHL}	HIGH to LOW propagation delay	A to B	—	3.2	_	3.3	_	3.4	ns
t _{PLH}	LOW to HIGH propagation delay	A to B		3.5		4.1	_	4.4	ns
t _{PHL}	HIGH to LOW propagation delay	B to A	_	3.0	_	3.6	_	4.3	ns
t _{PLH}	LOW to HIGH propagation delay	B to A		2.5		1.6	_	0.7	ns
t _{en}	enable time	OE to A; B		200	_	200	—	200	ns
t _{dis}	disable time	OE to A; no external load ^[2]		20		20		20	ns

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Symbol	Parameter	Conditions		V _{CC(B)}					
			2.5 V	± 0.2 V	3.3 V	± 0.3 V	5.0 V ± 0.5 V		
			Min	Мах	Min	Max	Min	Мах	
		OE to B; no external load	2]	20	_	20	_	20	ns
		OE to A		200		200	_	200	ns
		OE to B		200		200	_	200	ns
t _{TLH}	LOW to HIGH	A port	2.8	7.4	2.6	6.6	1.8	6.2	ns
	output transition time	B port	3.2	8.3	2.9	7.9	2.4	6.8	ns
t _{THL}	HIGH to LOW	A port	1.9	5.7	1.9	5.5	1.8	5.3	ns
	output transition time	B port	2.2	7.8	2.4	6.7	2.6	6.6	ns
t _{sk(o)}	output skew time	between channels	3]	0.7	_	0.7	_	0.7	ns
t _W	pulse width	data inputs	20		20	_	20	_	ns
f _{data}	data rate			50		50	_	50	Mbit/s
$V_{CC(A)} =$	3.3 V ± 0.3 V			-				1	
t _{PHL}	HIGH to LOW propagation delay	A to B			_	2.4		3.1	ns
t _{PLH}	LOW to HIGH propagation delay	A to B	_			4.2	_	4.4	ns
t _{PHL}	HIGH to LOW propagation delay	B to A	-		-	2.5	-	3.3	ns
t _{PLH}	LOW to HIGH propagation delay	B to A	_	_	—	2.5	-	2.6	ns
t _{en}	enable time	OE to A; B		_		200	_	200	ns
t _{dis}	disable time	OE to A; no external load	2]	_		15		15	ns
		OE to B; no external load	2]	_		15	_	15	ns
		OE to A				260	_	260	ns
		OE to B		_		200	_	200	ns
t _{TLH}	LOW to HIGH	A port	_	_	2.3	5.6	1.9	5.9	ns
	output transition time	B port	_	_	2.5	6.4	2.1	7.4	ns
t _{THL}	HIGH to LOW	A port		_	2.0	5.4	1.9	5.0	ns
	output transition time	B port	_	_	2.3	7.4	2.4	7.6	ns
t _{sk(o)}	output skew time	between channels	3]	_		0.7	_	0.7	ns
t _W	pulse width	data inputs		_	20	_	20	_	ns
f _{data}	data rate		_	_	_	50	_	50	Mbit/s

Table 10. Dynamic characteristics for temperature range -40 °C to +85 °C^[1]...continued Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 8; for wave forms see Figure 6 and Figure 7.

[1] t_{en} is the same as t_{PZL} and $t_{\text{PZH}}.$

 $\begin{array}{l} t_{dis} \text{ is the same as } t_{PLZ} \text{ and } t_{PHZ}.\\ \text{Delay between OE going LOW and when the outputs are actually disabled.}\\ \text{Skew between any two outputs of the same package switching in the same direction.} \end{array}$ [2] [3]

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Symbol	Parameter	Conditions		V _{CC(B)}						Unit
			ĺ	2.5 V	± 0.2 V	3.3 V :	± 0.3 V	5.0 V ± 0.5 V		
						Min	Max	Min	Мах	
V _{CC(A)} =	1.8 V ± 0.15 V									
t _{PHL}	HIGH to LOW propagation delay	A to B		_	5.8	_	5.9		7.3	ns
t _{PLH}	LOW to HIGH propagation delay	A to B		—	8.5	_	8.5	_	8.8	ns
t _{PHL}	HIGH to LOW propagation delay	B to A		—	5.5	_	5.7		5.9	ns
t _{PLH}	LOW to HIGH propagation delay	B to A		_	6.7	_	5.7		0.7	ns
t _{en}	enable time	OE to A; B			200	_	200		200	ns
t _{dis}	disable time	OE to A; no external load	[2]	_	30	—	30		30	ns
		OE to B; no external load	[2]		30	_	30		30	ns
		OE to A			250	_	250		250	ns
		OE to B			220	_	220		220	ns
t _{TLH}	H LOW to HIGH output transition time	A port		3.2	11.9	2.3	11.7	1.8	9.5	ns
		B port		3.3	13.5	2.7	11.4	2.7	9.5	ns
t _{THL}	HIGH to LOW output transition time	A port		2.0	7.4	1.9	7.5	1.7	16.7	ns
		B port		2.9	9.5	2.8	9.4	2.8	12.5	ns
t _{sk(o)}	output skew time	between channels	[3]		0.8	—	0.8		0.8	ns
t _W	pulse width	data inputs		20	_	20	_	20	_	ns
f _{data}	data rate			—	50	_	50		50	Mbit/ s
V _{CC(A)} =	2.5 V ± 0.2 V	1			1			1	1	
t _{PHL}	HIGH to LOW propagation delay	A to B		—	4.0	_	4.2		4.3	ns
t _{PLH}	LOW to HIGH propagation delay	A to B		—	4.4	_	5.2		5.5	ns
t _{PHL}	HIGH to LOW propagation delay	B to A		—	3.8	_	4.5		5.4	ns
t _{PLH}	LOW to HIGH propagation delay	B to A		—	3.2	-	2.0	_	0.9	ns
t _{en}	enable time	OE to A; B			200		200		200	ns
t _{dis}	disable time	OE to A; no external load	[2]		25	_	25		25	ns
		OE to B; no external load	[2]		25	_	25		25	ns
		OE to A		_	220	_	220		220	ns
		OE to B		_	220		220		220	ns

Table 11. Dynamic characteristics for temperature range -40 °C to +125 °C^[1] Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 8; for wave forms see Figure 6 and Figure 7.

Symbol	Parameter	V _{CC(B)}								
						3.3 V ± 0.3 V		5.0 V ± 0.5 V		
				Min	Max	Min	Max	Min	Max	
t _{TLH}	LOW to HIGH	A port		2.8	9.3	2.6	8.3	1.8	7.8	ns
	output transition time	B port		3.2	10.4	2.9	9.7	2.4	8.3	ns
t _{THL}	HIGH to LOW	A port		1.9	7.2	1.9	6.9	1.8	6.7	ns
	output transition time	B port		2.2	9.8	2.4	8.4	2.6	8.3	ns
t _{sk(o)}	output skew time	between channels	[3]	_	0.8	_	0.8	_	0.8	ns
t _W	pulse width	data inputs		20	_	20	_	20	_	ns
f _{data}	data rate				50	_	50		50	Mbit/ s
V _{CC(A)} =	3.3 V ± 0.3 V				1	J	1		1	
t _{PHL}	HIGH to LOW propagation delay	A to B		_		_	3.0	_	3.9	ns
t _{PLH}	LOW to HIGH propagation delay	A to B		_	—	_	5.3	_	5.5	ns
t _{PHL}	HIGH to LOW propagation delay	B to A		—	—	_	3.2	_	4.2	ns
t _{PLH}	LOW to HIGH propagation delay	B to A		—	_	_	3.2	_	3.3	ns
t _{en}	enable time	OE to A; B		_	_	—	200	—	200	ns
t _{dis}	disable time	OE to A; no external load	[2]	_	_	—	20	_	20	ns
		OE to B; no external load	[2]	_	_	_	20	_	20	ns
		OE to A			_	_	280	_	280	ns
		OE to B				_	220	_	220	ns
t _{TLH}	LOW to HIGH	A port		_	_	2.3	7.0	1.9	7.4	ns
	output transition time	B port			_	2.5	8.0	2.1	9.3	ns
t _{THL}	HIGH to LOW	A port		_	_	2.0	6.8	1.9	6.3	ns
	output transition time	B port				2.3	9.3	2.4	9.5	ns
t _{sk(o)}	output skew time	between channels	[3]	_	_	_	0.8	_	0.8	ns
t _W	pulse width	data inputs		_	_	20	_	20	_	ns
f _{data}	data rate			_	_	_	50	_	50	Mbit/ s

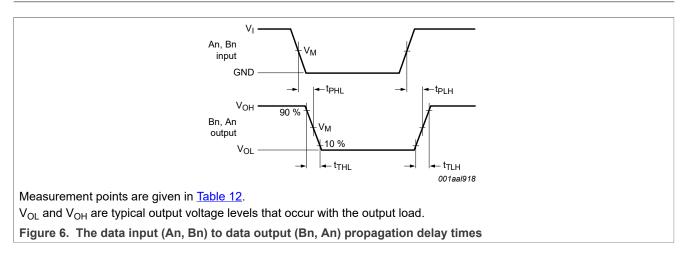
Table 11. Dynamic characteristics for temperature range -40 °C to +125 °C^[1]...continued Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 8; for wave forms see Figure 6 and Figure 7.

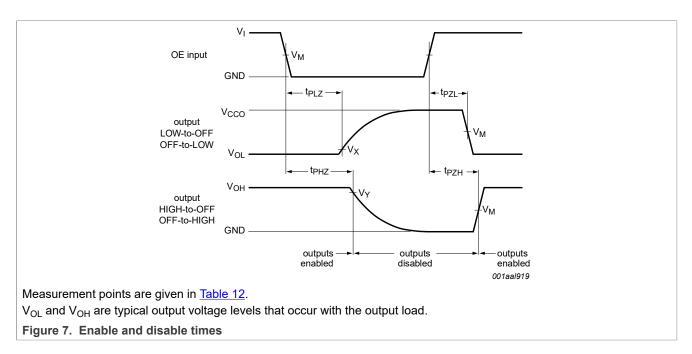
[1] t_{en} is the same as t_{PZL} and t_{PZH} .

 d_{is} is the same as μ_{L} and μ_{HZ} . Delay between OE going LOW and when the outputs are actually disabled.

[2] [3] Skew between any two outputs of the same package switching in the same direction.

12 Waveforms



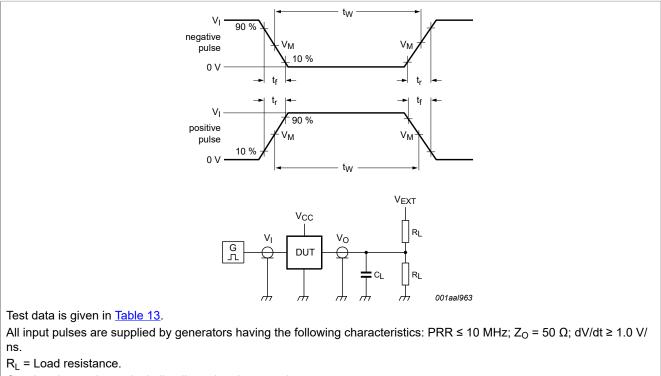


Supply voltage	Input	Output	Output				
V _{cco}	V _M	V _M	V _X	V _Y			
1.8 V ± 0.15 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} – 0.15 V			
2.5 V ± 0.2 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} – 0.15 V			
3.3 V ± 0.3 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	V _{OH} – 0.3 V			
5.0 V ± 0.5 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	V _{OH} – 0.3 V			

[1] V_{CCI} is the supply voltage associated with the input.

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 C_{L} = Load capacitance including jig and probe capacitance.

 V_{EXT} = External voltage for measuring switching times.

Figure 8. Test circuit for measuring switching times

Supply voltage		Input		Load		V _{EXT}		
V _{CC(A)}	V _{CC(B)}	V _I ^[1]	Δt/ΔV	CL	R _L ^[2]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	$t_{PZL}, t_{PLZ}^{[3]}$
1.65 V to 3.6 V	2.3 V to 5.5 V	V _{CCI}	≤ 1.0 ns/V	15 pF	50 kΩ, 1 MΩ	open	open	2V _{CCO}

 $\label{eq:VCCI} \mbox{is the supply voltage associated with the input.}$

For measuring data rate, pulse width, propagation delay, and output rise and fall measurements, $R_L = 1 M\Omega$; for measuring enable and disable times, $R_L = 50 K\Omega$.

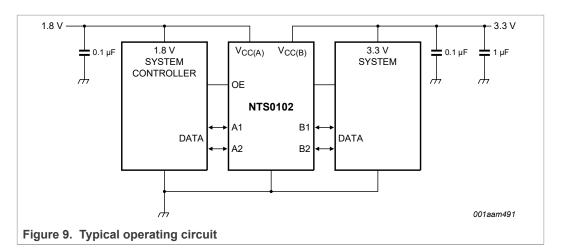
[3] V_{CCO} is the supply voltage associated with the output.

13 Application information

13.1 Applications

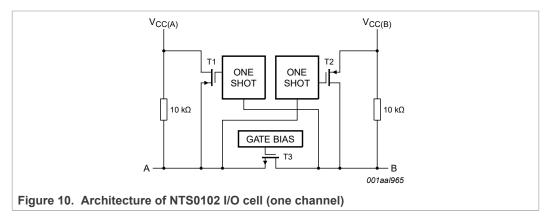
Voltage level-translation applications. The NTS0102 can be used in point-to-point applications to interface between devices or systems operating at different supply voltages. The device is primarily targeted at I^2C or 1-wire which use open-drain drivers, it may also be used in applications where push-pull drivers are connected to the ports, however the NTB0102 may be more suitable.

NTS0102



13.2 Architecture

The architecture of the NTS0102 is shown in <u>Figure 10</u>. The device does not require an extra input signal to control the direction of data flow from A to B or B to A.



The NTS0102 is a "switch" type voltage translator, it employs two key circuits to enable voltage translation:

- 1. A pass-gate transistor (N-channel) that ties the ports together.
- 2. An output edge-rate accelerator that detects and accelerates rising edges on the I/O pins.

The gate bias voltage of the pass gate transistor (T3) is set at approximately one threshold voltage above the V_{CC} level of the low-voltage side. During a LOW-to-HIGH transition, the output one-shot accelerates the output transition by switching on the PMOS transistors (T1, T2) bypassing the 10 k Ω pull-up resistors and increasing current drive capability. The one-shot is activated once the input transition reaches approximately V_{CCI}/2; it is de-activated approximately 50 ns after the output reaches V_{CCO}/2. During the acceleration time, the driver output resistance is between approximately 50 Ω and 70 Ω . To avoid signal contention and minimize dynamic I_{CC}, the user should wait for the one-shot circuit to turn-off before applying a signal in the opposite direction. Pull-up resistors are included in the device for DC current sourcing capability.

13.3 Input driver requirements

As the NTS0102 is a switch type translator, properties of the input driver directly effect the output signal. The external open-drain or push-pull driver applied to an I/O determines the static current sinking capability of the system; the max data rate, HIGH-to-LOW output transition time (t_{THL}), and propagation delay (t_{PHL}) are dependent upon the output impedance and edge-rate of the external driver. The limits provided for these parameters in the data sheet assume a driver with output impedance below 50 Ω is used.

13.4 Output load considerations

The maximum lumped capacitive load that can be driven is dependent upon the one-shot pulse duration. In cases with very heavy capacitive loading, there is a risk that the output will not reach the positive rail within the one-shot pulse duration.

To avoid excessive capacitive loading, and to ensure correct triggering of the oneshot, it's recommended to use short trace lengths and low capacitance connectors on NTS0102 PCB layouts. To ensure low impedance termination and avoid output signal oscillations and one-shot re-triggering, the length of the PCB trace should be such that the round trip delay of any reflection is within the one-shot pulse duration (approximately 50 ns).

13.5 Power up

During operation $V_{CC(A)}$ must never be higher than $V_{CC(B)}$, however during power-up $V_{CC(A)} \ge V_{CC(B)}$ does not damage the device, so either power supply can be ramped up first. There is no special power-up sequencing required. The NTS0102 includes circuitry that disables all output ports when either $V_{CC(A)}$ or $V_{CC(B)}$ is switched off.

13.6 Enable and disable

An output enable input (OE) is used to disable the device. Setting OE = LOW

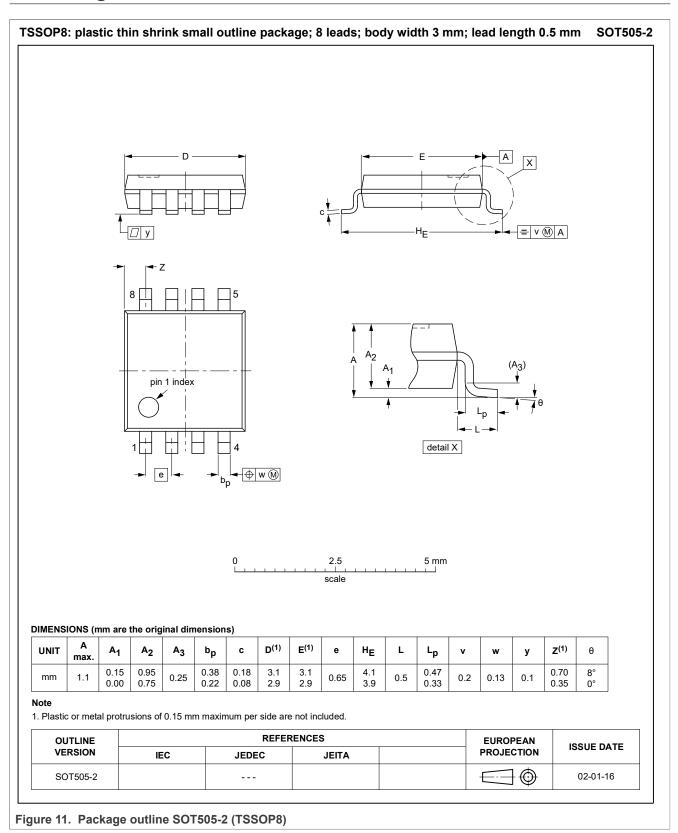
causes all I/Os to assume the high-impedance OFF-state. The disable time (t_{dis} with no external load) indicates the delay between when OE goes LOW and when outputs actually become disabled. The enable time (t_{en}) indicates the amount of time the user must allow for one one-shot circuitry to become operational after OE is taken HIGH. To ensure the high-impedance OFF-state during power-up or power-down, pin OE should be tied to GND through a pull-down resistor, the minimum value of the resistor is determined by the current-sourcing capability of the driver.

13.7 Pull-up or pull-down resistors on I/Os lines

Each A port I/O has an internal 10 k Ω pull-up resistor to V_{CC(A)}, and each B port I/O has an internal 10 k Ω pull-up resistor to V_{CC(B)}. If a smaller value of pull-up resistor is required, an external resistor must be added parallel to the internal 10 k Ω , this effects the V_{OL} level. When OE goes LOW the internal pull-ups of the NTS0102 are disabled.

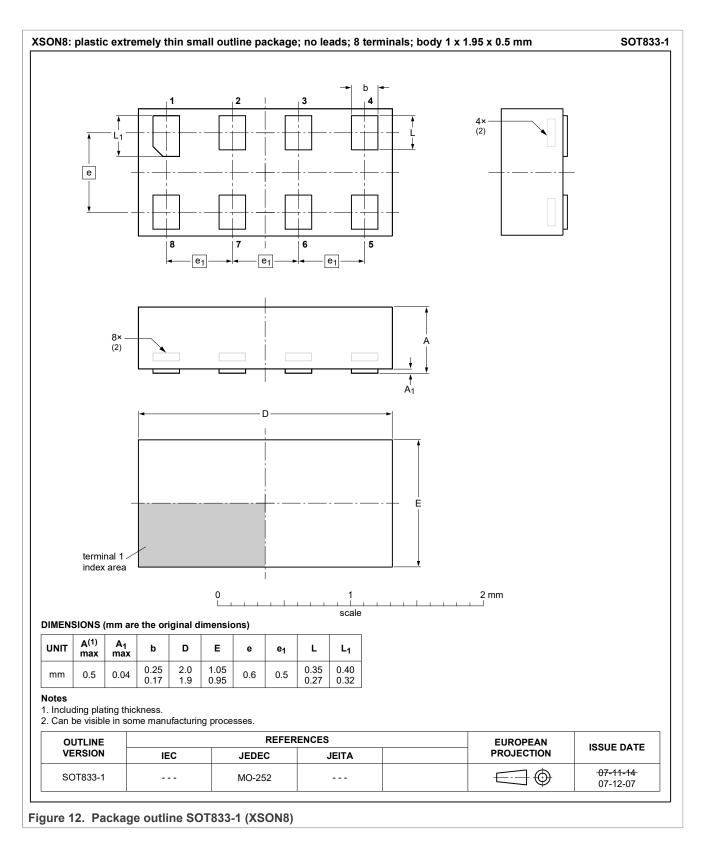
NTS0102

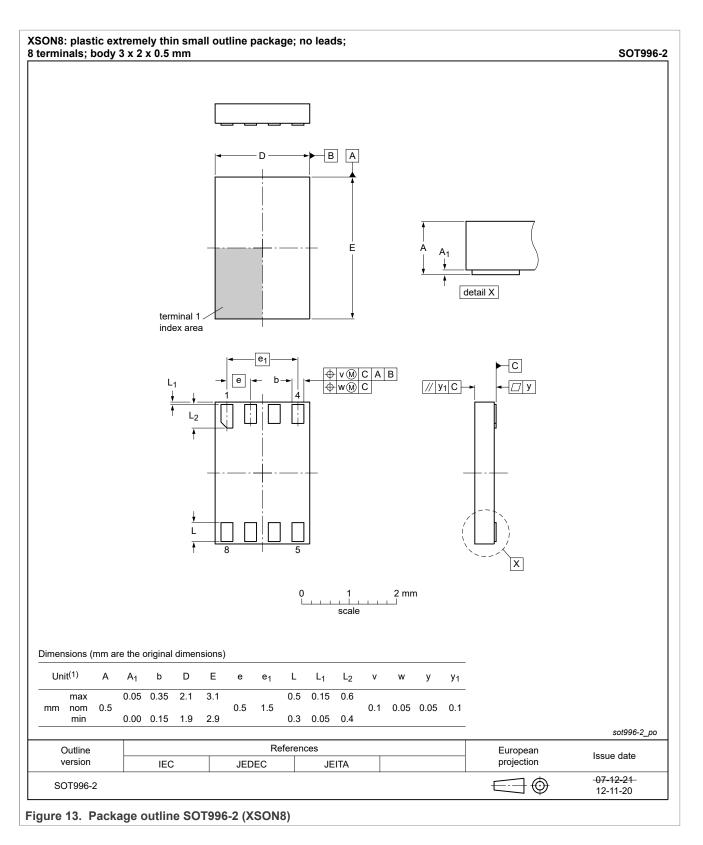
14 Package outline

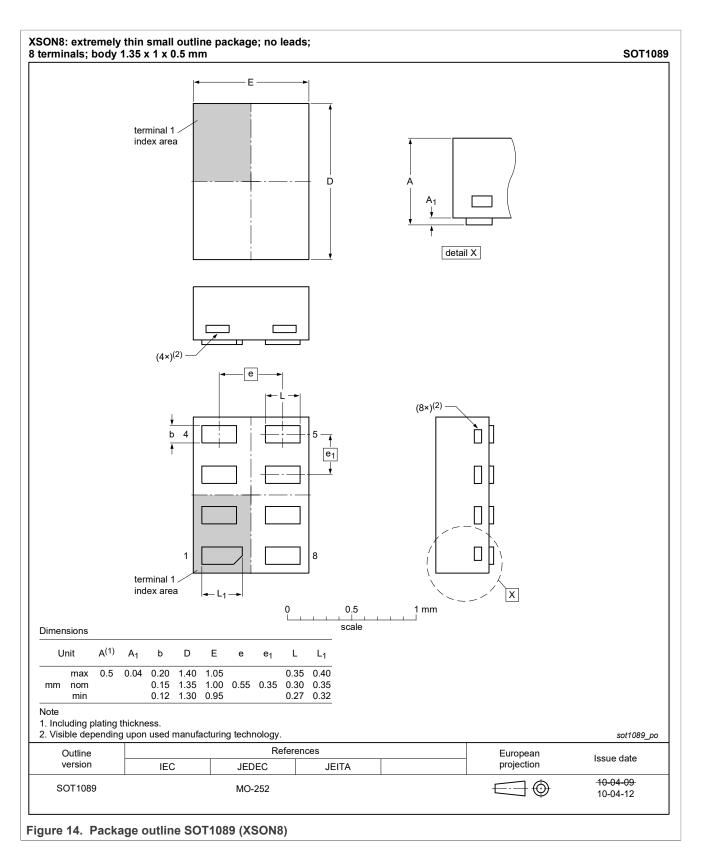


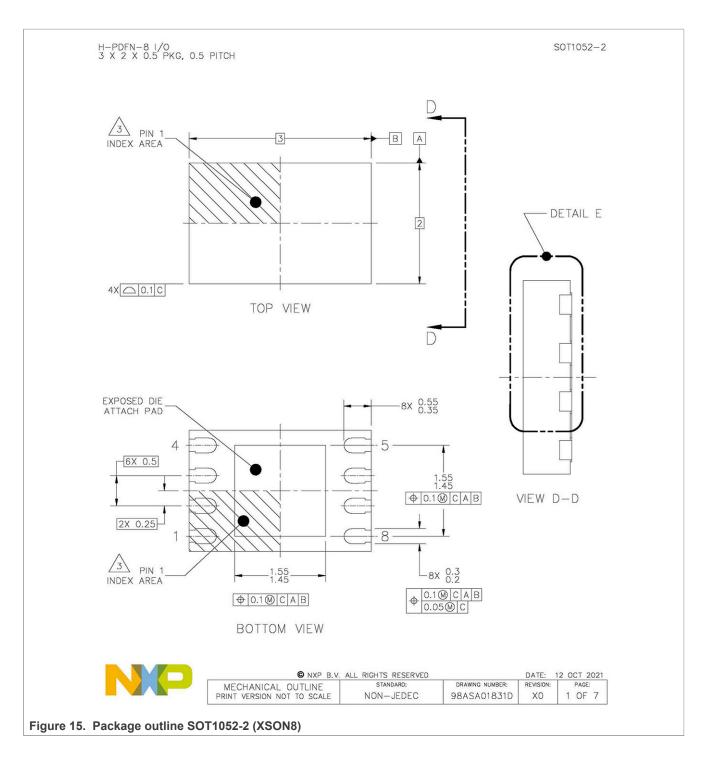
NTS0102 Product data sheet

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15 Abbreviations

Table 14. Abbreviations					
Acronym	Description				
CDM	Charged Device Model				
CMOS	Complementary Metal Oxide Semiconductor				
DUT	Device Under Test				
ESD	ElectroStatic Discharge				
GPIO	General Purpose Input Output				
НВМ	Human Body Model				
l ² C	Inter-Integrated Circuit				
ММ	Machine Model				
РСВ	Printed-circuit board				
PMOS	Positive Metal Oxide Semiconductor				
SMBus	System Management Bus				
UART	Universal Asynchronous Receiver Transmitter				
UTLP	Ultra Thin Leadless Package				

16 Revision history

Table 15. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NTS0102 v.4.1	20211112	Product data sheet		NTS0102 v.4
Modifications:	 NTS0102GU NTS0102TL: Temperature Section 4.1, Topside mark and Marking Section 4.1, ins Section 6.1 SOT1160-1: SOT1309-1: SOT1502-2: Section 6.2, Tage 	: removed row from table - 8: removed row from table inserted new row. range column: removed ter <u>Table 2</u> . king: added new column for table. serted new section and <u>Tab</u> Removed pinning figure. Removed pinning figure. Added pinning figure. <u>ble 3</u> , removed columns fro noved package outlines for	- device discontinued. E mperature range column marking and removed to le <u>2</u> . m table for SOT1160-1	n and inserted the column in top level Marking section
NTS0102 v.4	20130123	Product data sheet	_	NTS0102 v.3
NTS0102 v.3	20111117	Product data sheet	—	NTS0102 v.2
NTS0102 v.2	20110411	Product data sheet	-	NTS0102 v.1
NTS0102 v.1	20100921	Product data sheet	—	—

17 Legal information

17.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Dual supply translating transceiver; open-drain; auto direction sensing

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Dual supply translating transceiver; open-drain; auto direction sensing

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